

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	("3668095").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/28 16:29
L2	2	("6221788").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/28 17:54
L3	676	(438/682).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/28 17:54
L4	310	I3 and (oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 17:55
L5	11	I3 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:24
L6	691	438/664	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:24
L7	10	I6 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:26
L8	1324	438/655	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:26

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L9	21	l8 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:27
L10	918	438/649	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:27
L11	15	l10 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:27
L12	1002	438/669	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:27
L13	11	l12 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:27
L14	269	438/721	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:28
L15	4	l14 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:29
L16	868	257/536	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:29

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L17	230	I16 and (silicid\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:29
L18	4	I17 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:29
L19	2144	438/199	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:29
L20	46	I19 and (dry adj oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 18:30
S1	3	("2002064093").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 14:31
S2	3	("10223629").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 09:53
S3	2	("11067756").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 09:54
S4	3	("2002057154").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 09:55

EAST Search History

S5	2	("0434291").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 09:55
S6	2	("0434291").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 09:55
S7	2	("0757379").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 10:16
S8	2	("6221788").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 14:38
S9	1	("97013100").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 10:41
S10	1	("69628704").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 10:45
S13	405	(438/762).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 10:48
S15	0	S13 and drug	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 10:50

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S18	24960	(oxide near4 nitric\$)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 10:54
S19	3414	S18 and palladium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 10:55
S20	3045	S19 and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 11:16
S21	9	S20 and (vapor same drug)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 10:57
S22	1811	S20 and (silicon substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 11:17
S23	1157	S22 and heat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:54
S24	983	(438/770).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 12:55
S25	1	(semiconductor and solution) and (nitric adj acid) and (sulfuric adj acid) and (ozonic adj water) and (hydrogen adj peroxide) and (hydrochloric adj acid) and (aqueous adj ammonia) and (nitrohydrochloric adj acid) and (perchloric adj acid)and (boiling adj water)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:54

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S26	1	(semiconductor and solution) and (azeotropic adj nitric adj acid) and (nitric adj acid adj water) and (azeotropic adj sulfuric adj acid) and (azeotropic adj perchloric adj acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:58
S27	72	(semiconductor and film) and (aluminum and magnesium and nickel and chrome and platinum and palladium and tungsten and tantalum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 14:39
S28	138	(semiconductor and hydrogen adj gas) and (nitrogen and argon and neon and oxygen) and (water adj vapor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:25
S29	36959	(oxide adj film) and (silicon adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:36
S30	1	S29 and (nitric adj acid) and (sulfuric adj acid) and (ozonic adj water) and (hydrogen adj peroxide) and (hydrochloric adj acid) and (aqueous adj ammonia) and (nitrohydrochloric adj acid) and (perchloric adj acid)and (boiling adj water)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:35
S31	1615	S29 and (sulfuric adj acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:37
S32	77	S31 and (metal adj atoms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:38
S33	58	S32 and heat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:49

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S34	2	("5019891").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 15:49
S35	2	("6221788").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 11:09
S36	0	(semiconductor adj silicon) and (heat adj oxide) and (hydrogen adj gas) and (period adj range)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 09:08
S37	0	(semiconductor adj silicon) and (heat adj oxide) and (hydrogen adj gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 09:09
S38	2196	(silicon adj wafer) and (heat adj oxide film) and (hydrogen adj gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 09:10
S39	1436	S38 and minute	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 09:11
S40	1251	S39 and ranges	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 09:12
S41	242	S40 and (metal adj film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 09:12

EAST Search History

S42	2	("20050215070").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 14:39
S43	0	(silicon adj wafer) and (azeotropic adj sulfuric acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 14:41
S44	24640	(silicon adj wafer) and (azeotropic adj sulfuric acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:12
S45	16899	(silicon adj wafer) and (azeotropic adj sulfuric acid) and water	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 14:42
S46	3132	S45 and (oxide adj film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 14:46
S47	177	S46 and (metal adj atoms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 14:46
S48	1053	(silicon adj wafer) and (azeotropic adj mixture adj sulfuric acid adj water)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:13
S49	265	(silicon adj wafer) and (azeotropic adj mixture adj sulfuric acid adj water) and (oxide adj film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:20

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S50	85263	(azeotropic adj mixture adj sulfuric acid adj water)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:23
S51	131	S50 and (semiconductor adj film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:21
S52	335	S50 and (drug adj solution)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:27
S53	176	S52 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:29
S54	1	S52 and (oxide adj film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:41
S55	116905	(forming\$ near5 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:44
S56	233135	(formed\$ near5 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:43
S57	1561	S50 and S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:55

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S58	1	(semiconductor and solution) and (azeotropic adj nitric adj acid) and (nitric adj acid adj water) and (azeotropic adj sulfuric adj acid) and (azeotropic adj perchloric adj acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:54
S59	1	S56 and S58	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:54
S60	1	(azeotropic adj nitric adj acid) and (nitric adj acid adj water) and (azeotropic adj sulfuric adj acid) and (azeotropic adj perchloric adj acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 16:01
S61	1	S60 and S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:54
S62	6	S57 and 438/770	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:56
S63	1	S60 and (438/770)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 16:02
S64	0	S60 and (438/750,758,761,762,770)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 16:02
S65	2	("11067756").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 09:29

EAST Search History

S66	3	("10223629").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 09:35
S68	0	("43004291").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 09:36
S69	3	("2002064093").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 09:40
S70	2	("2002151521").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 09:41
S71	3	("2002022803").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 09:42
S72	2	("20020119327").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 09:22
S73	2	("5019891").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 09:57
S74	12	(silicon same substrate) and (hydrogen adj contain adj gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/22 10:09

EAST Search History

S75	2	("4526629").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 10:30
S76	2	("4684541").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 10:31
S77	2	("4782302").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/22 10:31
S78	745	(semiconductor and silicon) and (hydrogen adj nitrogen adj argon adj neon adj water vapor adj oxygen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:24
S79	52	S78 and (metal adj atoms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:34
S80	773	(hydrogen adj containing adj gas) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:59
S81	534	S80 and oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:36
S82	8	(hydrogen adj containing adj oxygen) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:46

EAST Search History

S83	4	("2002010490").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 09:44
S84	4	("2002010492").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 09:44
S85	19829	(hydrogen adj gases) and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:47
S86	11869	(hydrogen adj gases) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:47
S87	227517	(hydrogen adj containing gas) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:00
S88	13878	S87 and (metal same atoms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:01
S89	4472	(hydrogen adj nitrogen adj argon adj neon adj water vapor adj oxygen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:02
S90	2099111	S89 and silicon substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:02

EAST Search History

S91	2884	S89 and heat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:03
S92	441	S91 and platinum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:04
S93	161	S92 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 11:35
S94	2	("5144804").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 10:28
S95	2	("6120206").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 10:28
S96	3	("10223629").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 12:19
S97	2	("59174549").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 12:19
S98	4	("3668095").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 11:09